

N-Channel Advanced Power MOSFET

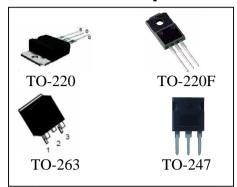
Features

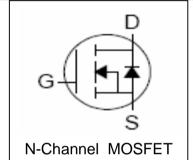
- 80V/190ARDS (ON)=3.9m Ω (Typ.) @ Ves=10V
- Avalanche Rated
- Reliable and Rugged
- Lead Free and Green Devices Available

Applications

- Automotive applications and a wide variety of other applications
- High Efficiency Synchronous in SMPS
- High Speed Power Switching

Pin Description





Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit			
Common Ra	tings (T _A =25°C Unless Otherwise Noted)		1	I		
V_{DSS}	Drain-Source Voltage	80	.,			
V_{GSS}	Gate-Source Voltage		±25	V		
TJ	Maximum Junction Temperature		175	°C		
T _{STG}	Storage Temperature Range		-55 to 175	°C		
Is	Diode Continuous Forward Current	190	А			
Mounted on	Large Heat Sink	•	1	1		
I _{DP}	300μs Pulsed Drain Current Tested	Tc=25°C	700 ^①			
	Continue Brain Courset	Tc=25°C	190	А		
I _D	Continue Drain Current	Tc=100°C	140	1		
P_{D}	Maximum Power Dissipation	Tc=25°C	400	w		
ıр	Maximum rower bissipation	Tc=100°C	220			
Rejc	Thermal Resistance -Junction to Case		0.45	9C/W		
R _θ JA	Thermal Resistance-Junction to Ambient	62.5	°C/W			
Drain-Sour	ce Avalanche Ratings		•	•		
Eas	Avalanche Energy ,Single Pulsed	2000	mJ			



Electrical Characteristics (T_A=25°C Unless Otherwise Noted)

0	D	Ta a 1 O a 11 a 11	RU190N08			11.74	
Symbol	Parameter	Test Condi	Mi			Max.	Unit
Static Cha	aracteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250	μΑ	80			V
	Zoro Cata Valtaga Drain Current	V _{DS} = 80V, V _{GS} =0			1		
I _{DSS}	Zero Gate Voltage Drain Current		T _J =85°C			30	μΑ
V _{GS(th)}	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_{DS}=25$	ΟμΑ	2	3	4	V
I _{GSS}	Gate Leakage Current	$V_{GS}=\pm 25V, V_{DS}=$	0V			±100	nA
R _{DS(ON)}	Drain-Source On-state Resistance	V _{GS} = 10V, I _{DS} =40)A		3.9	4.8	mΩ
Diode Cha	aracteristics						
V _{SD} ^③	Diode Forward Voltage	I _{SD} =40 A, V _{GS} =0V	′		0.8	1.3	V
trr	Reverse Recovery Time			68		ns	
qrr	Reverse Recovery Charge	Isb=40A, dlsb/dt=	100A/μs -		130		nC
Dynamic	Characteristics ^④		1		1	1	
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,I	=1MHz		1.0		Ω
C _{iss}	Input Capacitance	\/aa_0\/			6800		
C _{oss}	Output Capacitance	Vgs=0V, Vps= 30V,			1100		pF
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0M	Hz		490		
t _{d(ON)}	Turn-on Delay Time				38	70	
t _r	Turn-on Rise Time	VDD=35V, RL=359			22	41	ns
t _{d(OFF)}	Turn-off Delay Time	Ids= 1A, Vgen= 10 Rg=6Ω)V,		120	210	
t _f	Turn-off Fall Time				75	140	
Gate Cha	rge Characteristics	l			1		
Q_g	Total Gate Charge				155	220	
Q _{gs}	Gate-Source Charge	VDS=30V, VGS= 1 IDS=40A	0V,		45		nC
Q_{gd}	Gate-Drain Charge	100-70/1			48		

Notes: ①Pulse width limited by safe operating area.

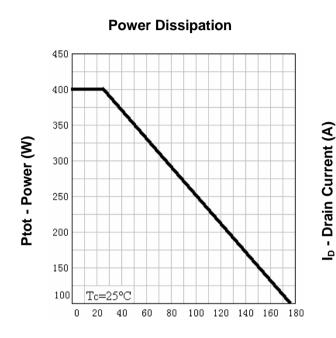
②Current limited by package(Limitation Current is 75A)

③Pulse test; Pulse width≤300μs, duty cycle≤2%.

④Guaranteed by design, not subject to production testing.



Typical Characteristics

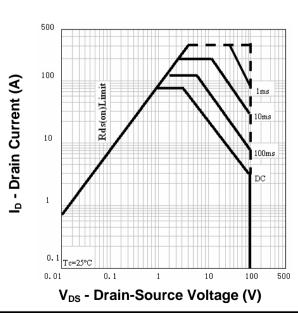


Tj - Junction Temperature (°C)

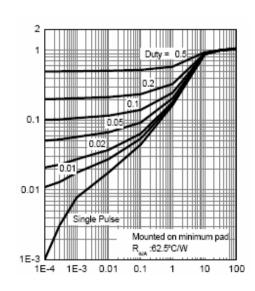
Drain Current 200 180 160 140 120 100 80 60 40 Limited By Package 20 0 Tc=25°C,Vg=10v 0 20 40 60 80 100 120 140 160 180

T_i - Junction Temperature (°C)

Safe Operation Area



Thermal Transient Impedance



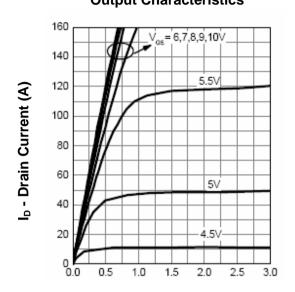
Square Wave Pulse Duration (sec)

Normalized Effective Transient



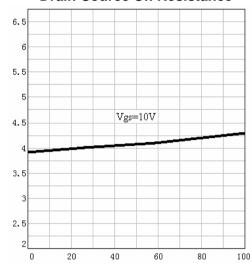
Typical Characteristics





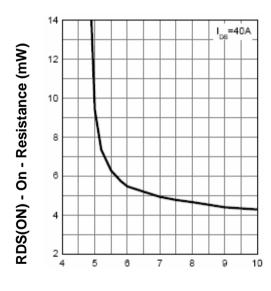
V_{DS} - Drain-Source Voltage (V)

Drain-Source On Resistance



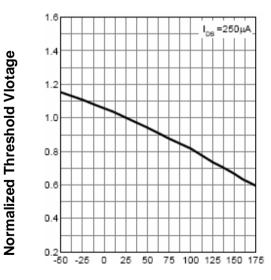
I_D - Drain Current (A)

Drain-Source On Resistance



VGS - Gate - Source Voltage (V)

Gate Threshold Voltage

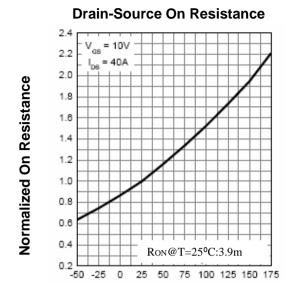


Tj - Junction Temperature (°C)

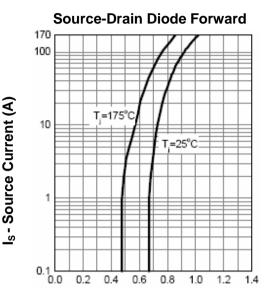
R_{DS(ON)} - On Resistance (m



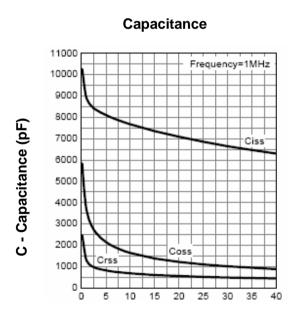
Typical Characteristics



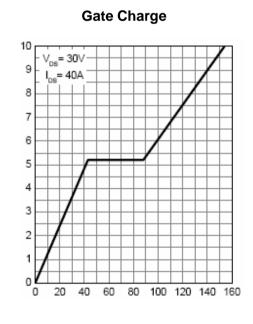
T_i - Junction Temperature (°C)



V_{SD} - Source-Drain Voltage (V)



V_{DS} - Drain-Source Voltage (V)

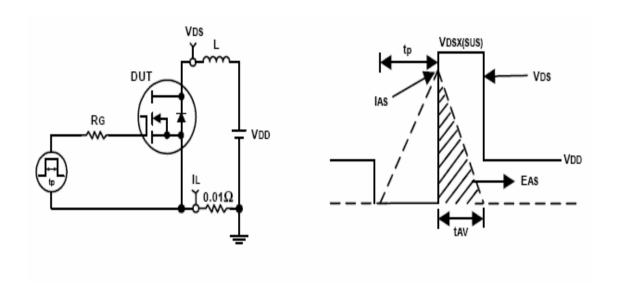


Q_G - Gate Charge (nC)

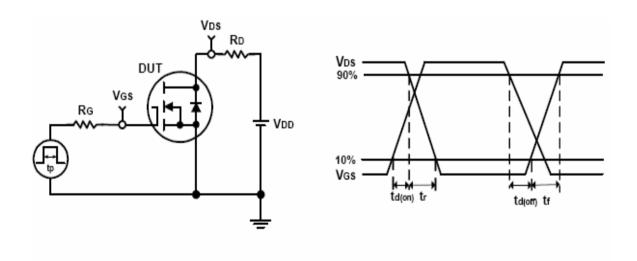
V_{gs} - Gate-Source Voltage (V)



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms





Ordering and Marking Information

RU190N08

Package (Available)

Q:TO-247; R: TO-220; S: TO-263

Operating Temperature Range

C: -55 to 175 °C
Assembly Material

G: Green & Lead Free Device

Packaging

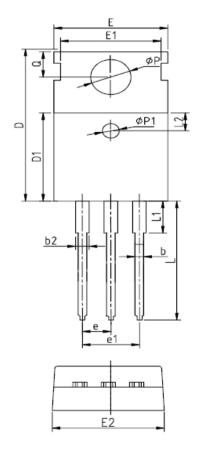
T: TUBE

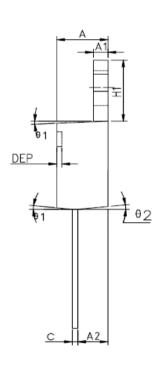
TR: Tape & Reel



Package Information

TO-220FB-3L



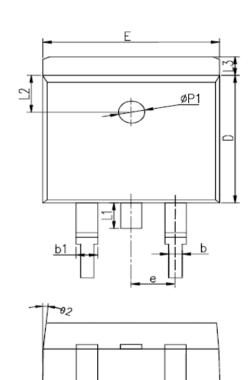


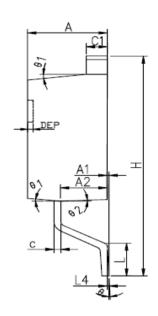
SYMBOL		MM		INCH			GIN ID OI	MM			INCH		
STWIDOL	MIN	NOM	MAX	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	Øp1	1.40	1.50	1.60	0.055	0.059	0.063
A1	1.27	1.30	1.33	0.050	0.051	0.052	e	2.54BSC		0.1BSC			
A2	2.35	2.40	2.50	0.093	0.094	0.098	e1	5.08BSC		0.2BSC			
b	0.77	1	0.90	0.030	-	0.035	H1	6.40	6.50	6.60	0.252	0.256	0.260
b2	1.23	-	1.36	0.048	-	0.054	L	12.75	-	13.17	0.502	-	0.519
С	0.48	0.50	0.52	0.019	0.020	0.021	L1	-	-	3.95	-	-	0.156
D	15.40	15.60	15.80	0.606	0.614	0.622	L2	2.50REF.			0.098REF.		
D1	9.00	9.10	9.20	0.354	0.358	0.362	Øр	3.57	3.60	3.63	0.141	0.142	0.143
DEP	0.05	0.10	0.20	0.002	0.004	0.008	Q	2.73	2.80	2.87	0.107	0.110	0.113
Е	9.70	9.90	10.10	0.382	0.389	0.398	θ 1	5°	7°	9°	5°	7°	9°
E1	-	8.70	-	-	0.343	-	θ 2	1°	3°	5°	1°	3°	5°
E2	9.80	10.00	10.20	0.386	0.394	0.401							

ALL DIMENSIONS REFER TO JEDEC STANDARD DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS



TO-263-2L



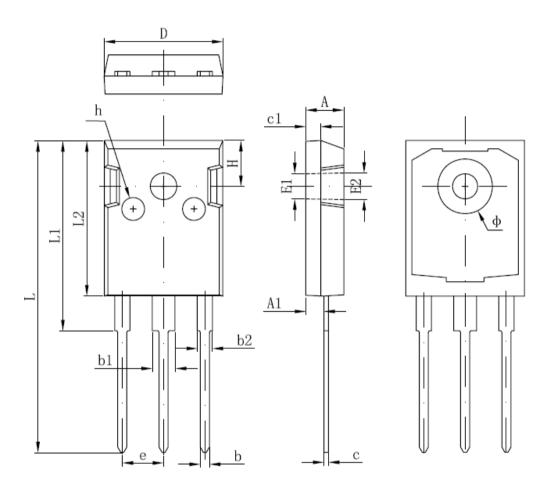


SYMBOL	MM			INCH			avn m av	MM			INCH		
SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	L	2.00	2.30	2.60	0.079	0.090	0.102
A1	0	0.10	0.25	0	0.004	0.010	L3	1.17	1.27	1.40	0.046	0.050	0.055
A2	2.59	2.69	2.79	0.102	0.106	0.110	L1	-	-	1.70	-	-	0.067
b	0.77	-	0.90	0.030	-	0.035	L4	0.25BSC			0.01BSC		
b1	1.23	-	1.36	0.048	-	0.052	L2	2.50REF.			0.098REF.		
c	0.34	-	0.47	0.013	-	0.019	θ	0°	-	8°	0°	-	8°
C1	1.22	-	1.32	0.048	-	0.052	θ 1	5°	7°	9°	5°	7°	9°
D	8.60	8.70	8.80	0.338	0.343	0.346	θ 2	1°	3°	5°	1°	3°	5°
Е	10.00	10.16	10.26	0.394	0.4	0.404	DEP	0.05	0.10	0.20	0.002	0.004	0.008
e		2.54BSC	!	0.1BSC		Øp1	1.40	1.50	1.60	0.055	0.059	0.063	
Н	14.70	15.10	15.50	0.579	0.594	0.610							

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TO-247



SYMBOL	MM		INCH		CVADOL	M	M	INCH	
STWIDOL	MIN	MAX	MIN	MAX	SYMBOL	MIN	MAX	MIN	MAX
A	4.850	5.150	0,191	0.200	E2	3.600 REF		0.142 REF	
A1	2.200	2.600	0.087	0.102	L	40.900	41.300	1.610	1.626
В	1.000	1.400	0.039	0.055	L1	24.800	25.100	0.976	0.988
b1	2.800	3.200	0.110	0.126	L2	20.300	20.600	0.799	0.811
b2	1.800	2.200	0.071	0.087	Φ	7.100	7.300	0.280	0.287
c	0.500	0.700	0.020	0.028	e	5.450 TYP		0.215 TYP	
c1	1.900	2.100	0.075	0.083	Н	5.980 REF.		0.235 REF.	
D	15.450	15.750	0.608	0.620	h	0.000	0.300	0.000	0.012
E1	3.500	REF.	0.138	REF.					

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